

ABSTRACT OF THE DISCLOSURE

A thin film transistor includes a substrate (1), a gate electrode (2) disposed in the substrate, a gate insulation layer (4) disposed on the substrate and gate electrode, a channel layer (5) disposed on the gate insulation layer, a source ohmic contact layer (6a) and a drain ohmic contact layer (6b) arranged on the channel layer and at the end of the channel layer, a source electrode (7a) disposed on the substrate and source ohmic contact layer, a drain electrode (7b) disposed on the substrate and drain ohmic contact layer.